

IN THE CLAIMS:

Please AMEND claim 28 as follows:

28. (Twice Amended) A semiconductor device, comprising:

a substrate;

a gate electrode provided on said substrate;

a diffusion region formed in said substrate adjacent to said gate electrode;

a side-wall insulation film formed on a side wall of said gate electrode;

a self-aligned contact hole defined by said side-wall oxide film and exposing said diffusion region; and

a silicide region formed selectively on a surface of said diffusion region;

wherein said semiconductor device further includes;

a first insulation film provided on said gate electrode so as to cover said side wall oxide film partially;

a second insulation film having a composition different from a composition of said first insulation film and provided on said first insulation film;

an interlayer insulation film deposited on said second insulation film;

a contact hole formed in said interlayer insulation film, said contact hole extending through said first and second insulation films and exposing said self-aligned contact hole;

said first insulation film contains H₂O with an amount smaller than about 2.4 wt%.
